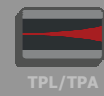


BROAD AREA LASER

GaAs Semiconductor Laser Diode
Single Emitter Structure

**General Product Information**

Product	Application
905 nm Broad Area Laser (Dual Emitter) for Pulse Mode Operation sealed TO-18 Housing (MIL qualified)	Sensing Metrology

Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-45		90
Operational Temperature at Case	T_C	°C	-45		90
Peak Current	$I_{F Peak}$	A			80
Reverse Voltage	V_R	V			1
Peak Output Power	$P_{opt Peak}$	W			65
Forward Voltage at Peak	V_F	V			15

Recommended Operational Conditions (Pulse Mode)

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_C	°C	-40		80
Forward Current	$I_{F Peak}$	A		72	
Output Power	$P_{opt Peak}$	W		56	

Characteristics at $T_{amb} 25\text{ °C}$, Pulse Mode, Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_C	nm	850	905	920
Spectral Width (FWHM)	$\Delta\lambda$	nm		10	
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.3	
Output Power	P_{ave}	mW		30	
Peak Output Power @ $I_F = 78\text{ A}$	$P_{opt Peak}$	W	50		
Threshold Current	I_{th}	A		3.0	
Operational Current @ $P_{opt Peak} = 50\text{ W}$	I_{op}	A		70	78

**Measurement Conditions / Comments**

Every condition of the Absolute Maximum Ratings has to be kept during operation

see Pulse Mode Conditions

f/1.7

see Pulse Mode Conditions

Measurement Conditions / Comments

under max. Pulse Mode Conditions

f/1.7

Measurement Conditions / Comments

f/1.7, under max. Pulse Mode Conditions

under Pulse Mode Conditions

under max. Pulse Mode Conditions

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Characteristics at T_{amb} 25 °C, Pulse Mode, Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Cavity Length	L	µm			1000
Stripe width	W _s	µm		400	
Spacing between Emitters	W _{spacing}	µm		200	
Stripe Pitch	W _{pitch}	µm		600	
Dual Emitter Width	W _{total}	µm		1000	
Divergence parallel (FWHM)	$\Theta_{ }$	°	7	10	13
Divergence perpendicular (FWHM)	Θ_{\perp}	°	25	30	35
Polarization				TE	
Spectral Mode (longitudinal)				Multi Mode	

Measurement Conditions / Comments
one emitter only
center to center of the dual emitters
total width of the dual emitter
E field perpendicular to plane B (see drawing on p. 3)

Pulse Mode Conditions

Parameter	Symbol	Unit	min	typ	max
Pulse Length	t _p	ns	50		200
Pulse Repetition Rate	RR	s ⁻¹	1		3000
Duty Cycle	D	%			0.06

Measurement Conditions / Comments

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We focus on power.

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Single Emitter Structure



Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d_{EP}	mm		2.4	
Excentricity of Emission Center	R	mm			0.2
Pin Length	l	mm		19.0	

Measurement Conditions / Comments

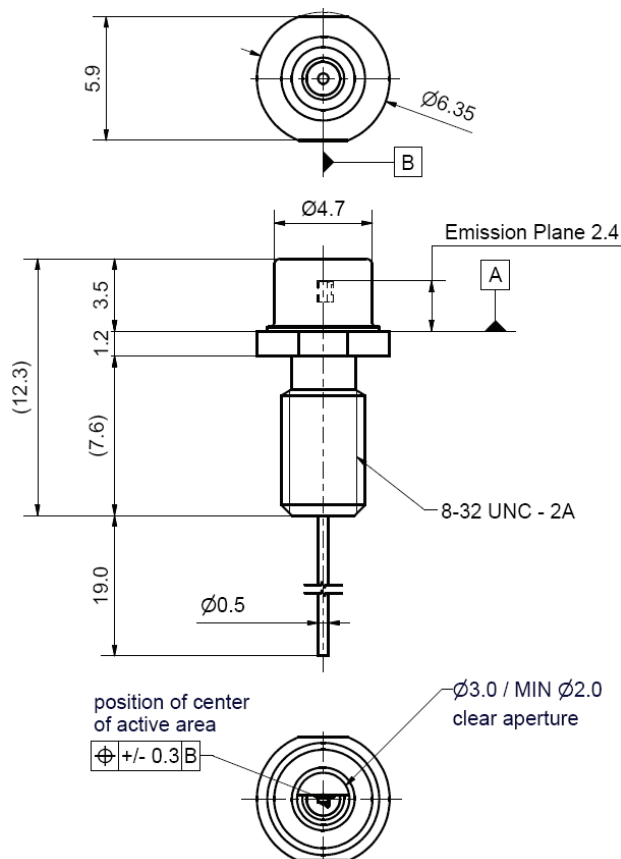
reference plane A: top side of TO header

reference B: center of outer diameter of header

Package Pinout

Laser Anode (+)	Pin
Laser Cathode (-)	Case

Package Drawings



hermetically sealed Package:

Leak Rate $< 5 \cdot 10^{-8}$ atm.cc./s

acc. MIL-STD-883E

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We focus on power.

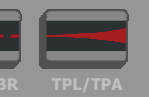
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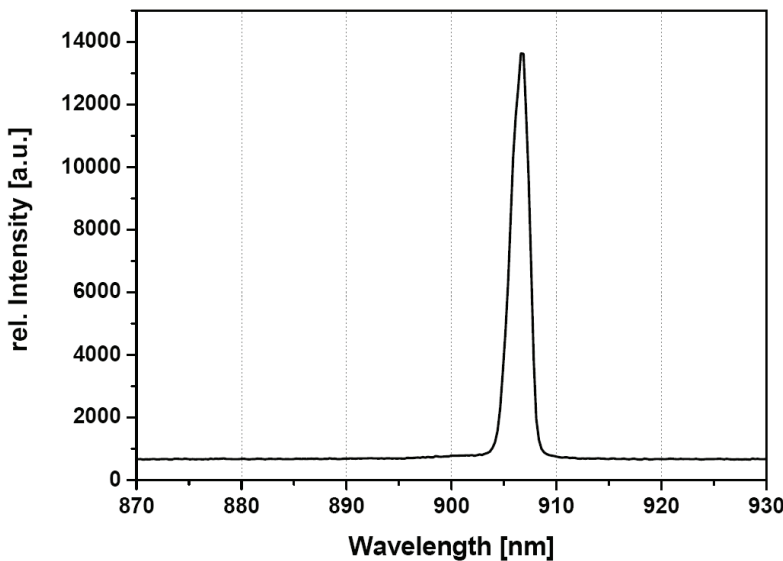
BROAD AREA LASER

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Single Emitter Structure



Typical Measurement Results

Spectrum



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

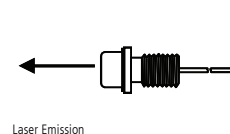
Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The BAL diode type is known to be sensitive against thermal stress. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.



IEC 60825-1



Complies with 21 CFR 1040.10 and 1040.40